

Polyimide product portfolio overview:

Non-photosensitive materials and Permanent glue materials

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FUJIFILM Electronic Materials (Europe) N.V.

Business Department





FFEM PI/PBO product portfolio

Non-photosensitive polyimides

- Pre-imidized polyimides
 - Patterning by RIE etch
 - Low temperature cure, low shrinkage
- Polyamic acid polyimides
 - Patterning with photoresist.
 Pattern transfer during TMAH develop step
- Low temperature cure polyimides
 - · Patterning with RIE etch
 - · EHS friendlier

Negative tone, solvent developable polyimides

- Standard cure material (350°C)
- Buffercoat for WB/FC packages
- Core product with medium Tg and medium CTE values
- High Tg, low CTE material
- Large film thickness range
- EHS friendlier solution

Negative tone, Low temperature cure polyimides, solvent developable

- Low temperature cure material (350°C down to 180°C)
- RDL dielectric or buffercoat for Wafer Level Packages
- · Low residual stress material
- · Large cured film thickness ranges
- Mask, stepper or LDI patternable
- Available in several coating techniques
- EHS friendlier solution

Positive tone TMAH developable polybenzoxazole

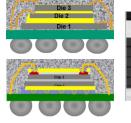
- High photospeed material
- · Advanced resolution
- EHS friendlier solution

Polyimide & PBO ancillaries

- Developer & rinse solvents
- Cup rinse, edge bead remover solvents
- Rework stripper for exposed and non-exposed polyimide
- Special adhesion promotors

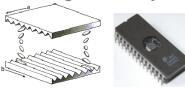
Typical applications of non-photosensitive polyimides

Component adhesive – glue 3D IC stacking

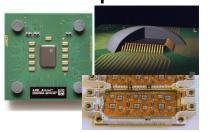




LCD alignment layer



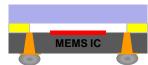
Glob top & underfill encapsulation





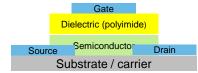
Adhesive – glue MEMS packages





Gate Insulator

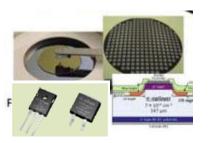
Organic electronics



Flexible PI substrate



DielectricsPower devices



Non-photosensitive polyimides product portfolio

Technology platform	Available grades	Key material properties
Pre-imidized polyimide-amide system	Durimide® 32A	NMP containing Low shrinkage material Medium cure temperature Patterning by RIE
Polyamic acid system	Durimide® 116A	NMP containing Patterning by photoresist development step Standard temperature cure
Polyamic ester PI precursor	LTG 12-52	EHS friendlier (NMP/NEP-free, halogen-free) Low temperature cure Large cure film thickness range Patterning by RIE
	LTG 12-32*	High Tg and low CTE version of LTG 12-52

^{*} Ongoing R&D development

Durimide[®] 32A (Pre-imidized polyimide-amide)

Non-photosensitive, pre-imidized polyamide-imide system

Product	Viscosity	CFT	Patterning
DUR 32A	700 cSt	1 – 11 µm	Dry etch process

Chemical structure

Major applications

- Junction coating for discrete devices Fully imidized polyimide-amide
- Glob top applications
- General passivation
- LCD alignment layers

Key features

- Low shrinkage upon bake
- No high temperature cure
- Good mechanical properties
- Patterning using dry etch process
- · Reworkable, solvent soluble

Cured Film Property	275°C	300°C	350°C
Young Modulus (GPa)	2.8	2.8	3.3
Tensile Strength, UTS (MPa)	196	184	184
Elongation (%)	74%	60%	56%
Glass transition, Tg (°C)	283	282	300
Thermal decomposition temperature (°C)	> 480°C	> 480°C	> 480°C
Thermal expansion, CTE (ppm/°C)	52	58	53
Dielectric strength, RT/50%RH (V/µm)	325	325	325

Typical Process conditions				
Preteatment	Dehydration bake or O ₂ -flash			
Spin coat PI	7 -25 μm CFT			
Cure	Oven with N ₂ purge			
Patterning	Coat wit photoresist or hardmask			
Transfer pattern into PI	RIE or O ₂ plasma			
Remove PR or hardmask	Wet or dry processing			

Note: export-restricted material.

Export licence and end-user statement required.

Durimide® 116A (Polyamic-acid system)

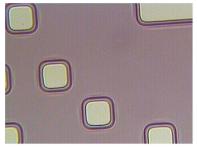
Non-photosensitive, polyamic-acid system

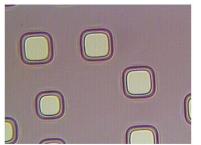
Product	Viscosity	CFT	Patterning
DUR 116A	12,000 cSt	4 – 10 μm	Positive photoresist (TMAH development)

Chemical structure

Cured Film Properties (350°C/60 min)	Data
Young Modulus (GPa)	3.3
Tensile Strength, UTS (MPa)	260
Elongation (%)	80%
Glass transition, Tg (°C)	371
Thermal decomposition temperature (°C)	> 590
Thermal expansion, CTE (ppm/°C)	32
Dielectric strength, RT/50%RH (V/µm)	325

• PI patterning with photoresist. Pattern transfer during TMAH development step





Pretreatment
Spin:
Soft bake
Patterning

Developing (pattern PI)
PR strip
Cure

Typical process conditions

Dehydration bake and/or O₂-flash
4000 rpm / 30 sec (CFT ~ 3.2 μm)
60 sec @ 110°C + 60 sec @ 130°C

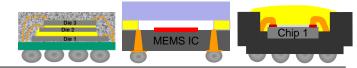
Coat photoresist. Softbake & exposure photoresist.
Typical 1.5 – 2.5 μm PR.
Puddle 1 x 60 sec with TMAH 2.38wt%

Wet process (solvent)
1 hour @ 350 to 400°C

SBFT: 9.9 µm

CFT: 5 µm

LTG 12-52 Low temperature cure PI (glue)



Non-photosensitive, low temperature cure polyimide

Product	Coating solvent	Viscosity (cSt)	CFT (µm)	CTE (ppm/°C)	Patterning	
LTG 12-52	GBL/DMSO	5800 – 6400	5 – 25	± 53	Dry etch process	

				LTG	12-52	
MATERIAL PROPERTIES				230°C 3h	200°C 3h	180°C 3h
	Modulus	GPa	2.3	2.5	2.6	2.6
Mechanical	Elongation at break (strain)	%	> 85	> 85	75	60
properties (Tensile test)	Tensile strength	MPa	195	185	180	160
	Tensile stress at yield	MPa	115	115	118	117
Material	Tg, tanδ	°C	240	235	230	220
properties (DMA & TMA)	CTE	ppm/°C	48	53	54	55
Weight loss	Weight loss Temperature (2%wt)	°C	405	310	305	285
(TGA)	Weight loss Temperature (5%wt)	°C	435	340	335	325

Typical applications:

- · Permanent adhesive/glue
 - Special applications Image sensors, SAW, high power devices...
 - WL capping, 3D WLCSP...
- As a glob top/encapsulant material to protect tdevice or wire bond (mold compound replacement).

Key features

- EHS friendly formulation
 - NMP-free and halogen-free
- · Based on polyimide polymer backbone
 - Resistant to high working temperatures
- · Low or/and high temperature cure applicable
 - Designed for lower cure temperature down to 180°C
- Excellent material properties at low & standard temperature cure
 - Excellent mechanical properties
 - · Adhesion force on different materials
- · High viscosity range
 - Large bondline thickness possible
- Low outgassing

LTG 12-32 (*) Low temperature cure PI (glue)

Non-photosensitive, low temperature cure polyimide precursor

Product	Coating solvent	Viscosity (cSt)	CFT (µm)	CTE (ppm/°C)	Patterning
LTG 12-52	GBL/DMSO	5800 - 6400	5 – 25	± 53	Dry etch process
LTG 12-32 (*)	GBL/DMSO	5800 - 6400	5 – 25	± 30	Dry etch process

Key features

- High Tg, low CTE material
- EHS friendly formulation
 - NMP-free and halogen-free
- · Based on polyimide polymer backbone
 - · Resistant to high working temperatures
- Low or/and high temperature cure applicable
 - Designed for lower cure temperature down to 180°C
- · Excellent material properties at low & standard temperature cure
 - Excellent mechanical properties
 - · Adhesion force on different materials
- · High viscosity range
 - Large bondline thickness possible
- Low outgassing

			LTG	12-32	LTG ²	12-52
	MATERIAL PROPERTIES		1h 350°C	3h 200°C	1h 350°C	3h 200°C
	Mechanical	Modulus (GPa)	2.9	2.9	2.3	2.6
	properties (Tensile test)	Elongation at break (%)	> 50%	2.9 2.3 2.6 > 50% > 85% 75% > 150 195 180 > 275 240 230 35 48 54	75%	
	(Terisile test)	Stress (MPa)	> 150	> 150	195	180
	Material	Tg, tanδ (°C)	> 350	> 275	195 180 240 230 48 54	
(properties (DMA & TMA)	CTE (ppm/°C)	27	35	48	54
re		Dielectric Constant 1MHz, 50% RH	3.3		3.3	3.3
	Electrical properties	Dissipation factor 1 MHz	0.007		< 0.01	< 0.01
		Dielectric strength, V/µm	> 345		1h 3h 3h 200°C 350°C 200°C 9 2.3 2.6 2.6 2.6 2.6 2.6 2.6 2.6 2.6 2.6 2.6	> 340
	Moisture upta	ake (wt%)			± 1.2	± 1.2

Typical **buffercoat or RDL layer** process flow - LTG series



Coat or dispense:

Wafer level glue: Adjust spin speed to change bond line thickness

Soft bake: gentle removal of casting solvents

- Typical process
- 120 to 300 sec at 120 160°C

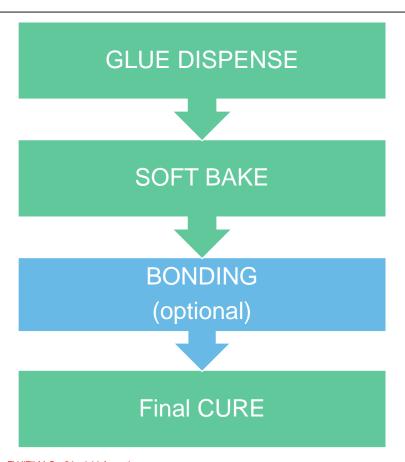
Final cure profile:

- Typical cure cycle: 180 to 250°C for 90 to 180 min
- Ramp-up/down rate: 3 to 5 min
- Rapid cure profile is possible

Patterning of the LTG polyimide layer

- Photoresist coating and patterning
- RIE transfer photoresist pattern into the PI-LTG film

Typical **bonding** process flow - LTG series



Coat or dispense:

- Die attach: pattern dispenser
- Dispense (glob top) in package cavity
- Wafer level glue: Adjust spin speed to change bond line thickness

Soft bake: gentle removal of casting solvents

- Typical process
- 120 to 300 sec at 120 160°C

Bonding: Die or component to substrate

 Minimum 10°C above soft bake temperature – Viscous elastic region of glue – good adhesion

Final cure profile:

- Typical cure cycle: 180 to 250°C for 90 to 180 min
- Ramp-up/down rate: 3 to 5 min
- Rapid cure profile is possible

Comparison non-photosensitive polyimides

	Durimide® 32A	Durimide [®] 116A	LTG 12-52
POLYMER TYPE	Pre-imidized amide-imide system	Polyamic acid system	Polyamic ester system
CASTING SOLVENT	NMP/Xylene	NMP	GBL/DMSO
POLYIMIDE PATTERNING	O ₂ or O ₂ /CF ₄ RIE plasma	Aqueous development with photoresist	O ₂ or O ₂ /CF ₄ RIE plasma
CURED FILM THICKNESS RANGES	1 – 11 μm	4 – 10 μm	5 – 25 μm
SHELF LIFE	36 months	12 months	12 months

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Comparison non-photosensitive polyimides – Cured film properties

	Durimide [®] 32A	LTG ·	12-52
Parameters	Cure 200 – 350°C	Cure condition 180 min / 200°C	Cure condition 90 min / 350°C
Ultimate Tensile Strength (MPa)	180	> 175	> 200
Young's Modulus (GPa)	2.8	3.0	3.0
Tensile Elongation at Break (%)	> 50%	> 50%	> 70%
Glass Transition Temperature (Tg by DMA, °C)	280	230	255
Coefficient of Thermal Expansion (CTE, ppm/°C)	~ 50	~ 55	~ 50
Decomposition Temperature (°C)	> 480°C	> 500°C	> 500°C

LTG 12-52 & Durimide® 32A yield very similar material properties.



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